

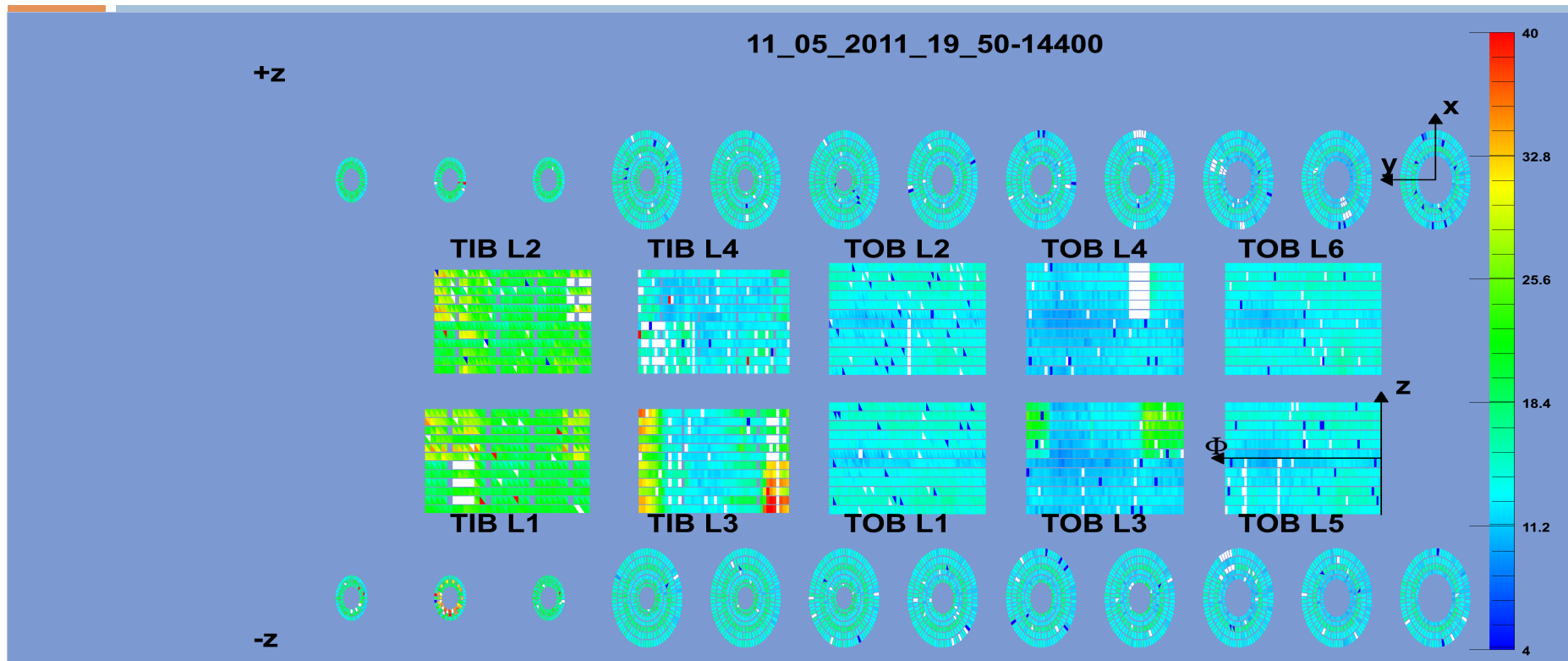
CMS SILICON STRIP TRACKER: RADIATION DAMAGE STUDIES

- LEAKAGE CURRENT MEASUREMENTS
- DEPLETION VOLTAGE MEASUREMENTS

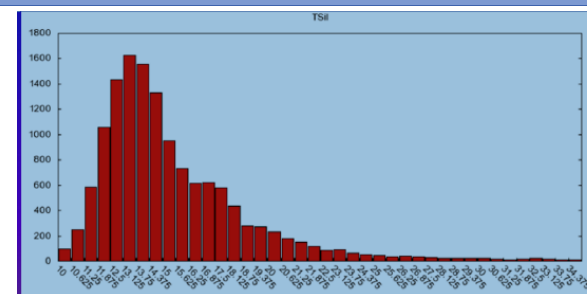
Leakage Current

- Power supply HV lines measure current supplied to several modules (3 to ~ 10) with $< 1\mu\text{A}$ precision
- Temperature of sensors is varying across the Strip Tracker but it is measured at module level
 - ▣ large variety of modules, silicon geometries and thermal contacts with cooling pipes
 - ▣ Comparison are done for current densities (normalization with volume) scaled to a temperature of 20C
- Detector Control Unit (DCU) every module, measures Silicon Sensor Temperature and Leakage current
 - ▣ Measurements rely on calibration constant taken in lab

Silicon Detector Temperature



Peak at 14C, but average Temperature different among different Subdetector (TIB, TOB, TEC, TID) and higher for Back-to-Back modules. Also some uncooled parts showing higher temp [30-40C]





Data from PS

4

WEB-based online tool

- No dedicated measurement
- Standard DB query

Power supply I value, begin of each fill (10min)

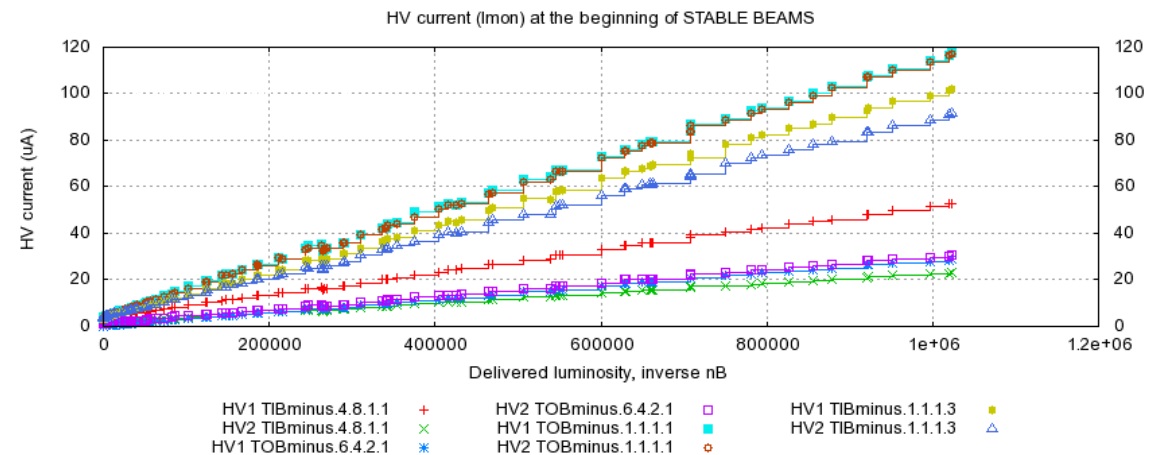
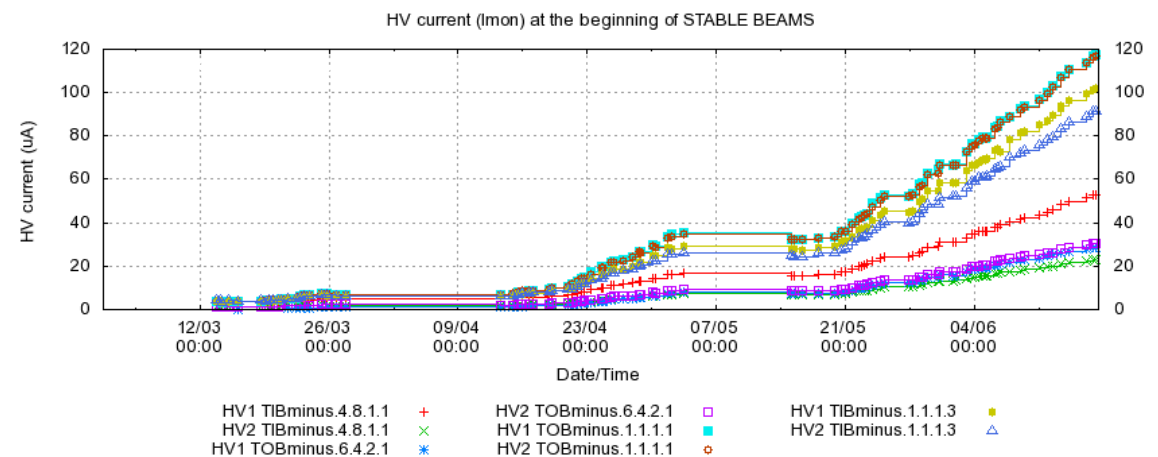
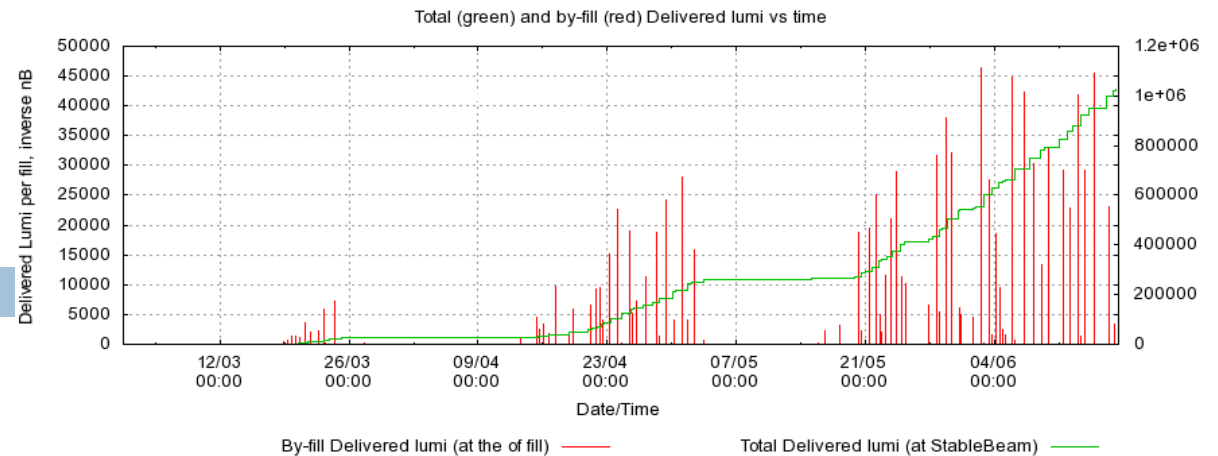
- Different layers – different ϕ
- Different # of modules
- Different T

→ different curves

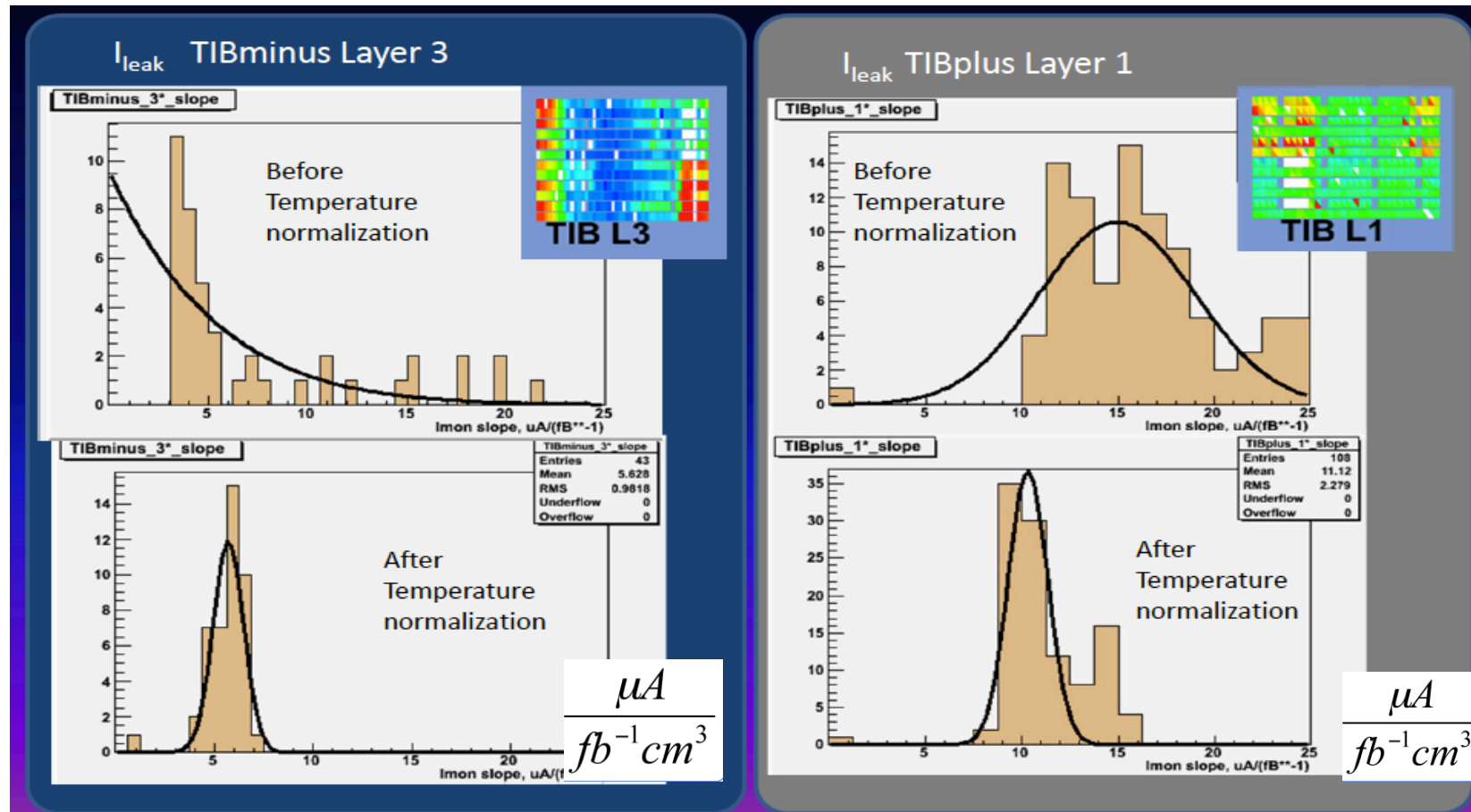
Offline analysis

- Normalize volume & T
- Normalize to slope

$[\mu\text{A}/1\text{fb}]$

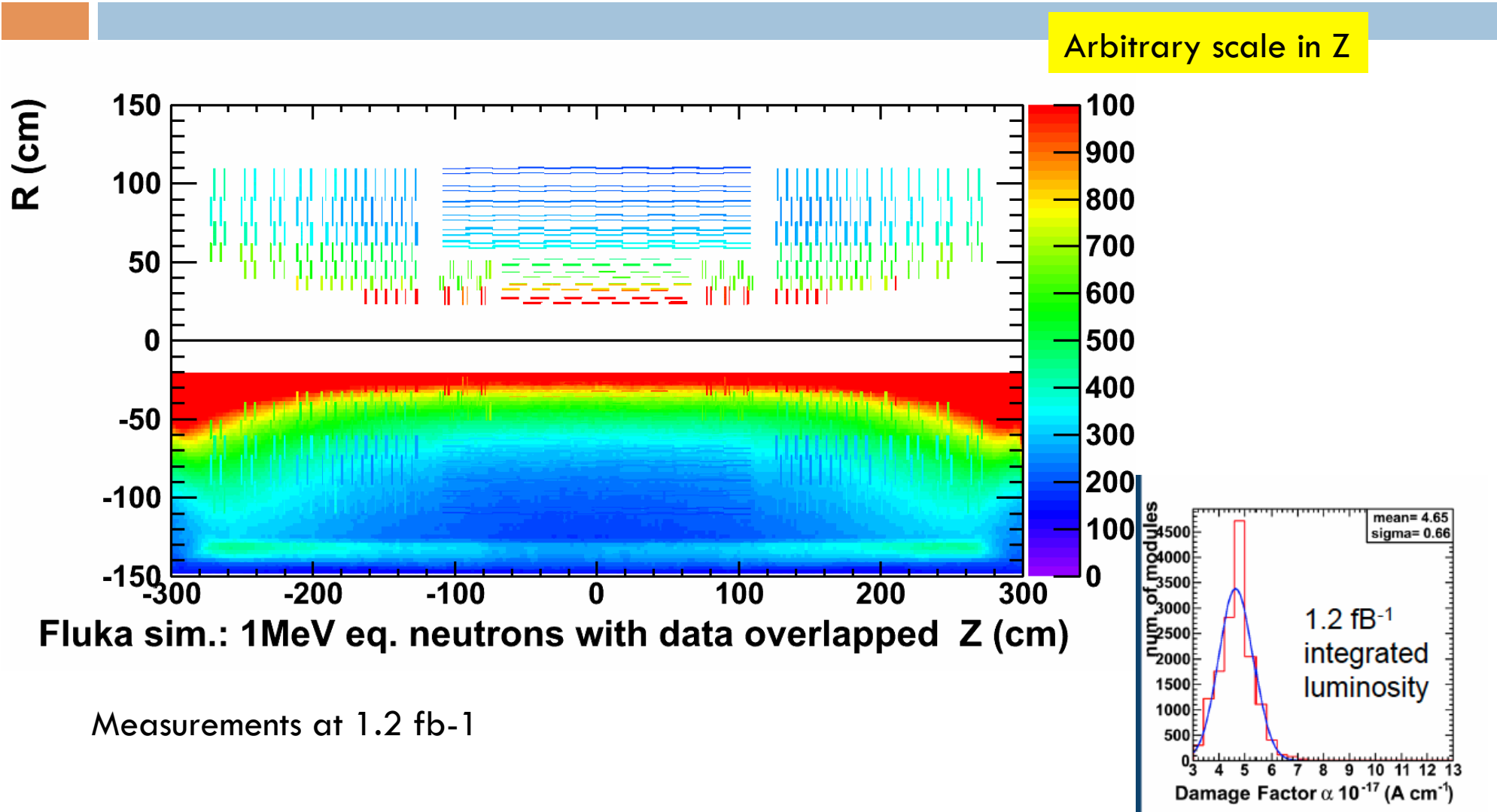


Temperature (and Volume) Normalization

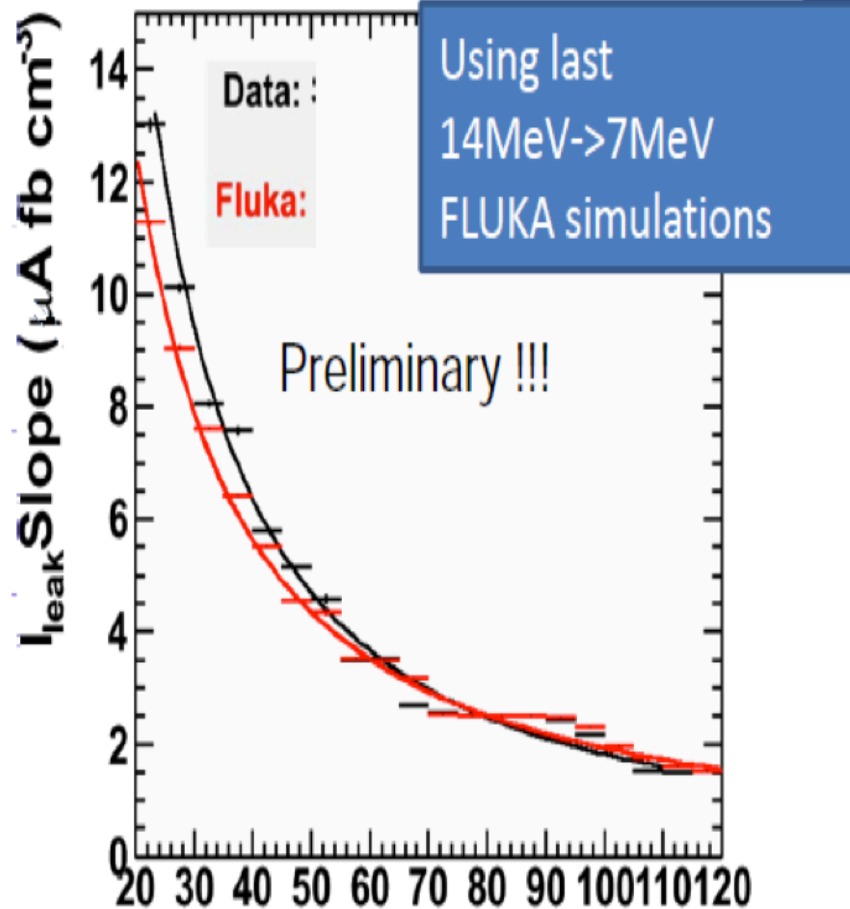


If measurements of T-sil are missing then Slope is not shown here. Some filtering on bad Measurements is done, but can be improved

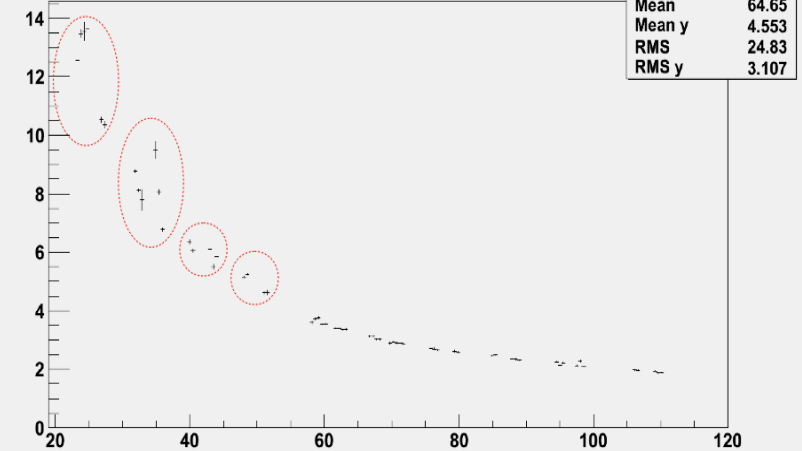
Relative comparison with Simulation



Radial Dependency

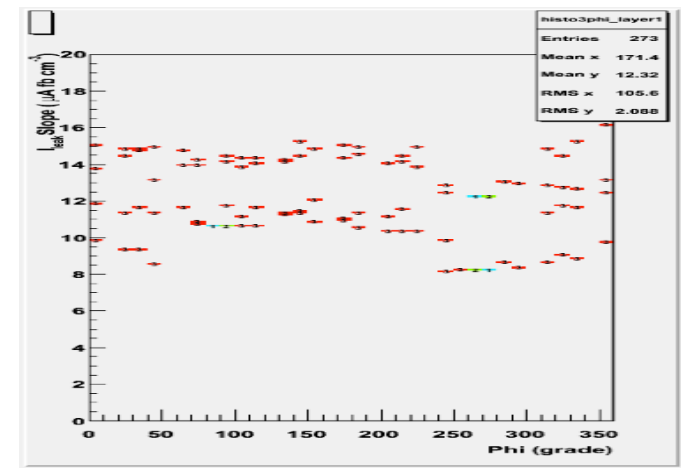


Looking with higher binning



histo3_prof	
Entries	6406
Mean	64.65
Mean y	4.553
RMS	24.83
RMS y	3.107

Studying a Φ structure in L1 internal.
Back-to-back Modules with different temp

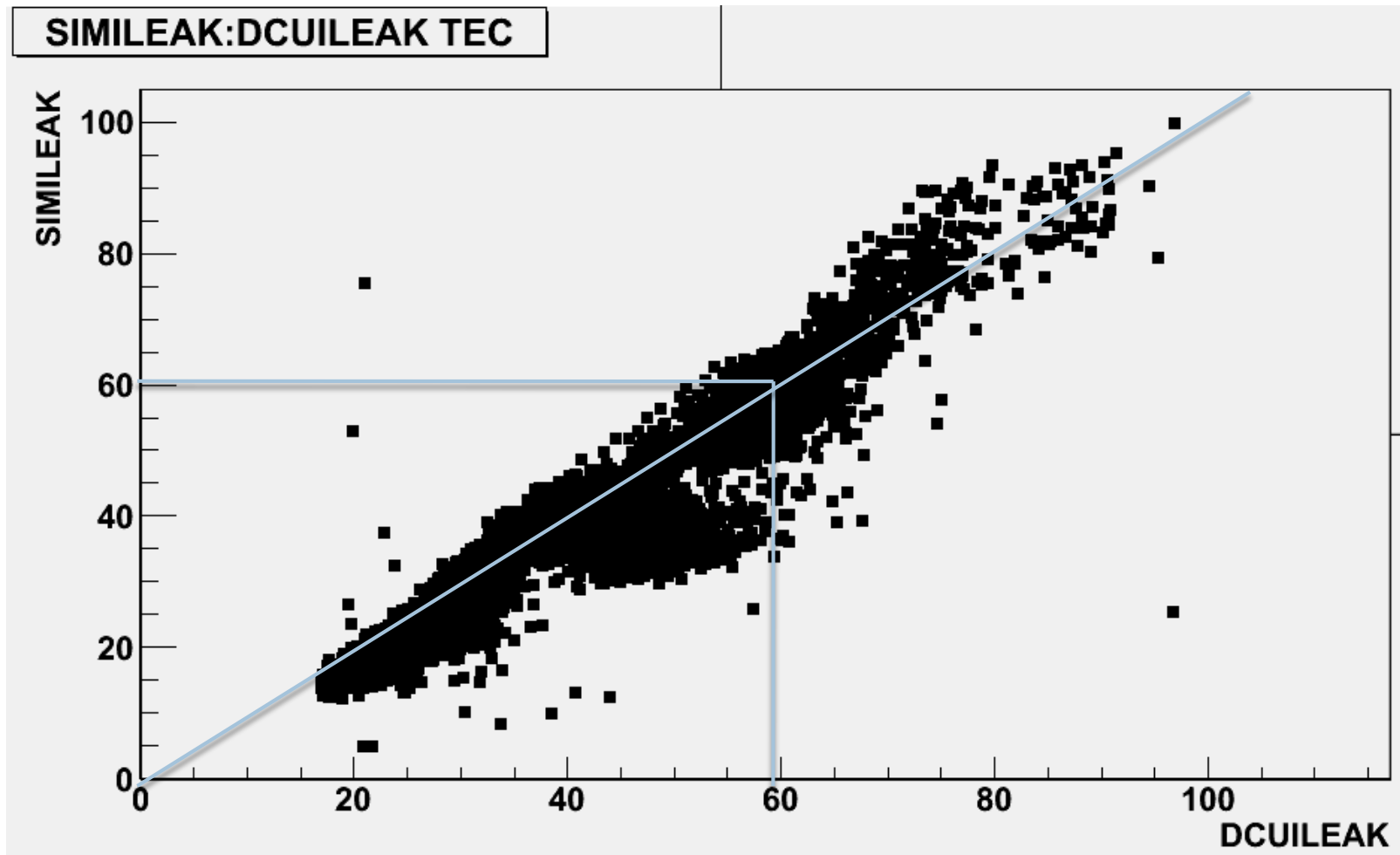


histo3phi_layer1	
Entries	273
Mean x	171.4
Mean y	12.32
RMS x	105.6
RMS y	2.085

Detailed comparison Data - Simulation

- Fluence taken from FLUKA
- Luminosity treated at per day level
 - ▣ Temperature are taken @ module level, using DCU
 - ▣ Temperature variations taken into account at per day level (Technical Stop, etc...)
- Comparison with Data using DCU leakage currents
- In this study we are very dependent on DCU calibrations and of course on FLUKA simulation

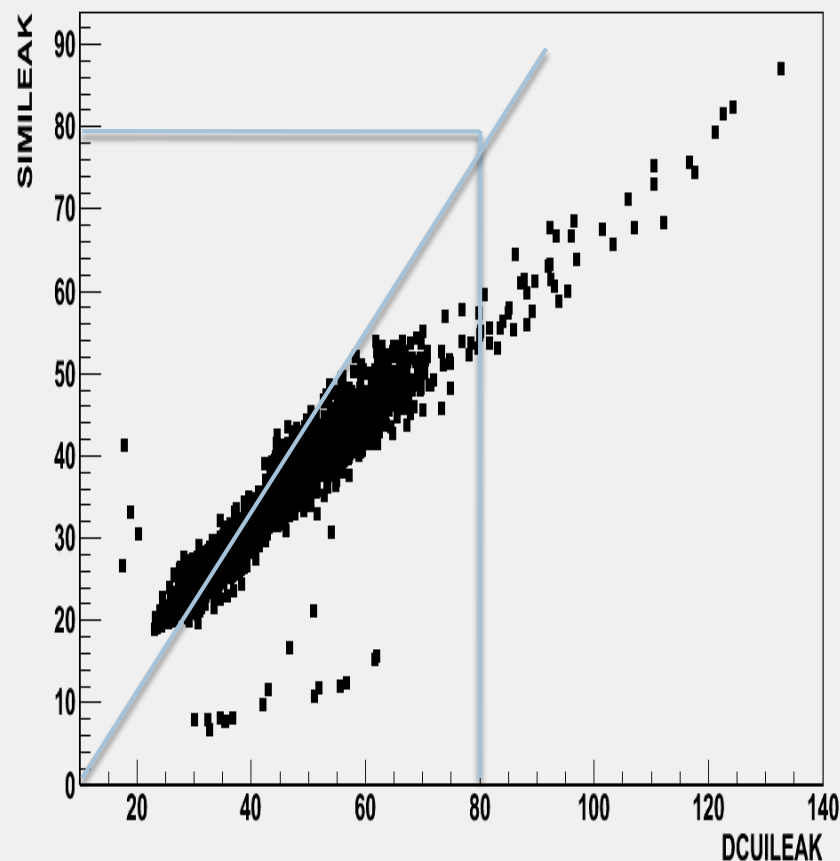
Simulation vs Measurement @ modules level (uses DCU data) - TEC case



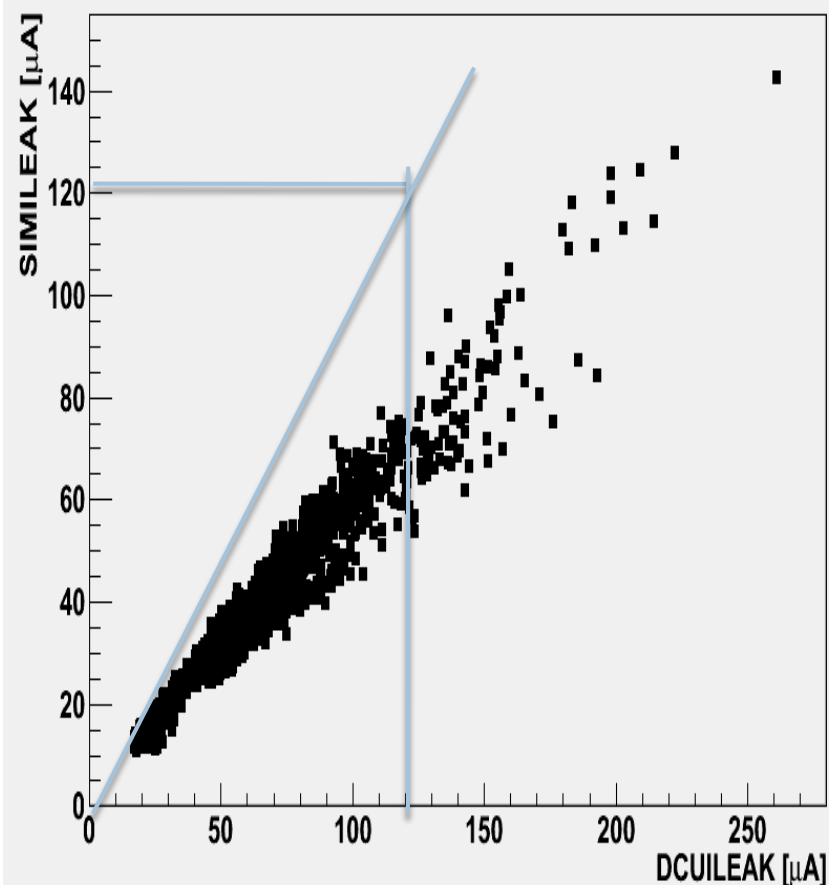
CMS Silicon Strip Tracker: Radiation Damage

Inner and Outer Barrel

SIMILEAK:DCUILEAK TOB



SIMILEAK:DCUILEAK TIB



We suspect that the Temperature measurements is affected by non-linearity at the beginning of ADC range of the DCU (high temperatures with respect to measurements at lab)

CMS Silicon Strip Tracker: Radiation Damage

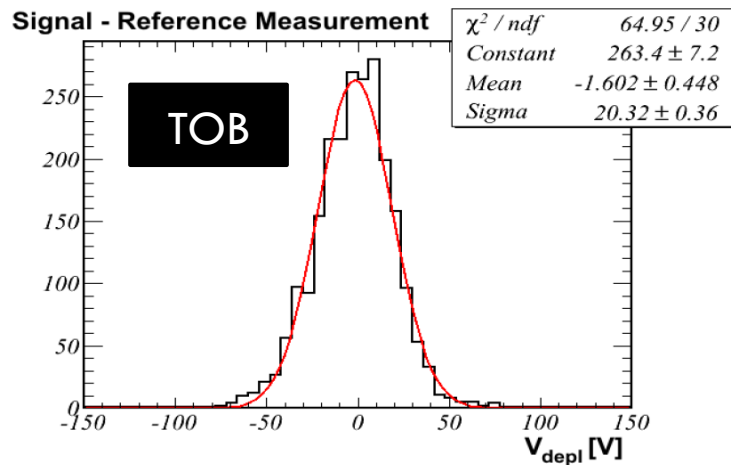
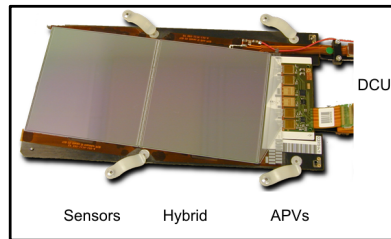
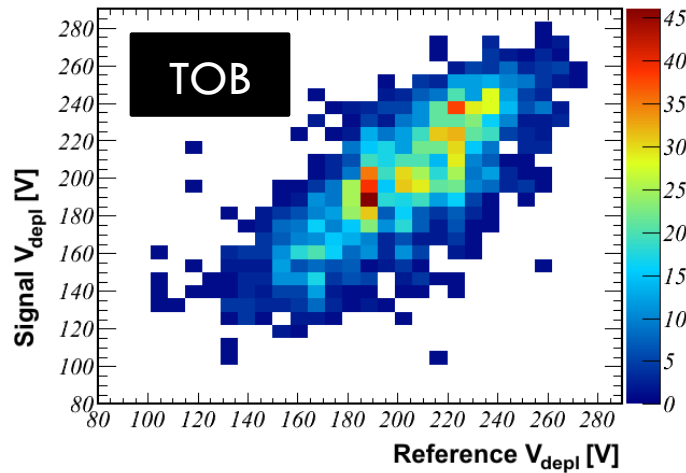
Depletion Voltage: measurements

- Signal vs Bias Voltage (HV scan)
 - ▣ Depletion voltage measurement
 - ▣ Done during collisions

- Noise vs Bias Voltage
 - ▣ Can be done during no beam activities

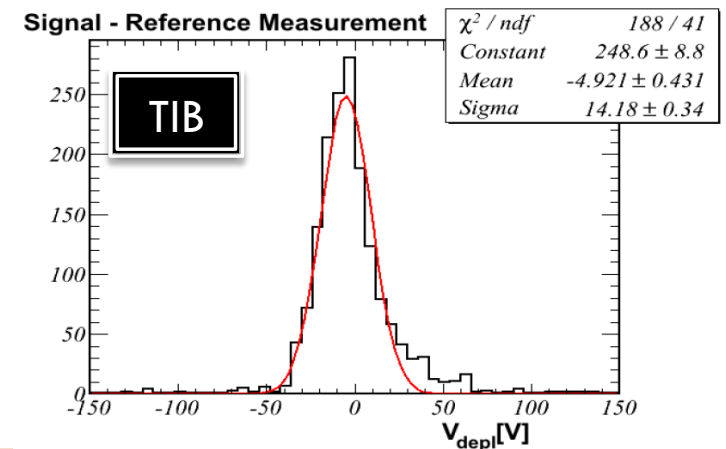
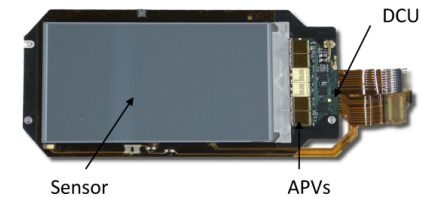
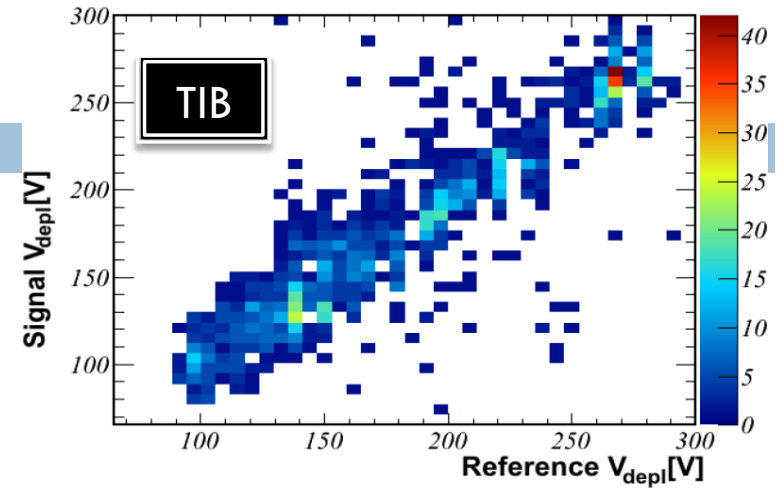
- **Up to 2 fb⁻¹ no evidence of change... as expected**
 - ▣ New HV scan before HL physics

Signal vs. voltage (during STABLE BEAM)



Very good agreement
between the results
from the signal scan
and the reference
measurements
(especially in TIB partition
with only one sensor per
module)

→
Anchor
measurement for
the future



Within to the accuracy of the measurement “no” significant change in Vdep is visible so far (Feb11).

Summary and Conclusions

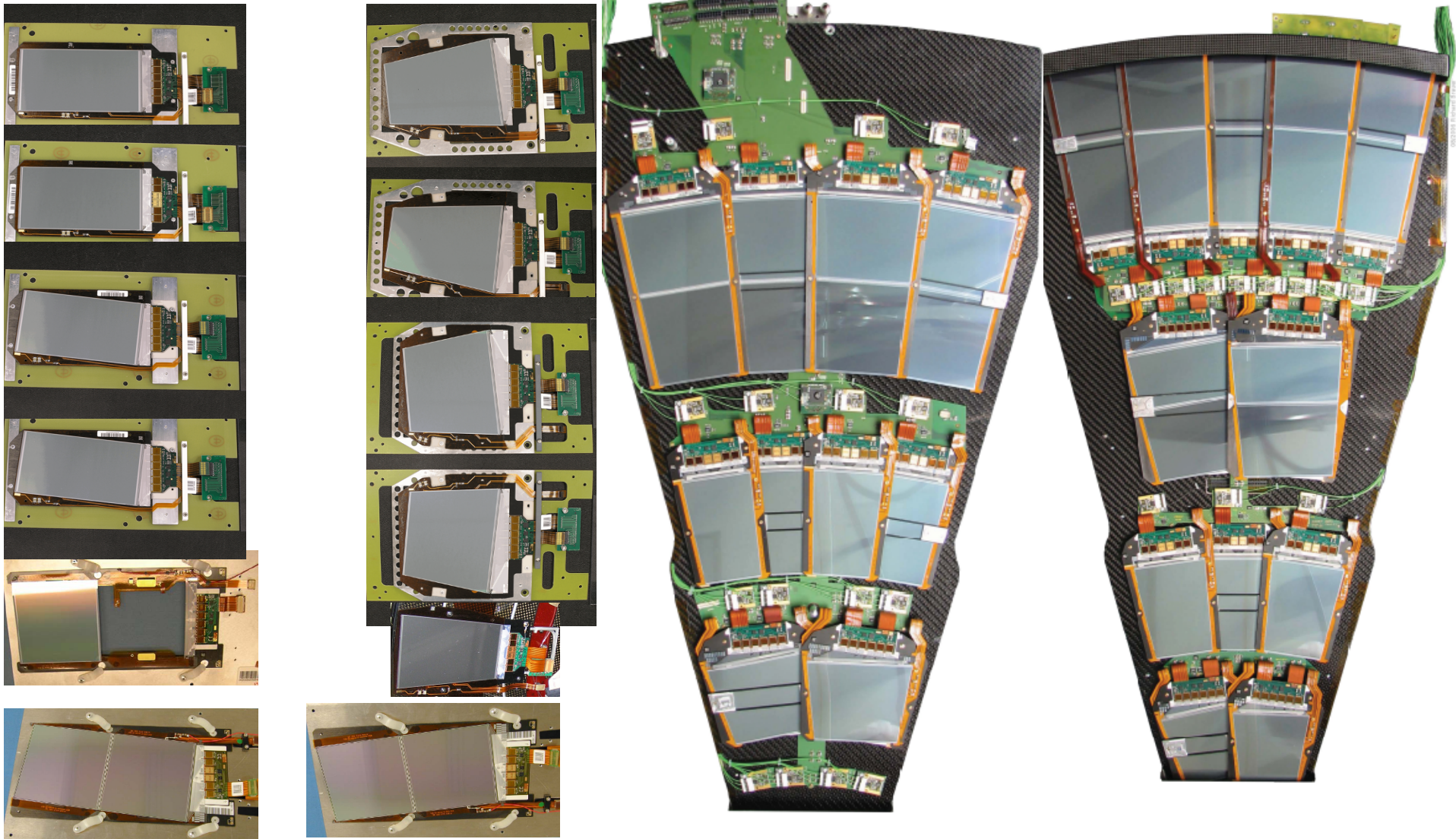
- Effects seen on Leakage current
 - Temperature variations across detector
 - Scaling for T-sil and Volume applied
 - Linear behaviour clearly seen (I_{leak} vs Luminosity)
 - Geometry dependence investigated
 - First comparison with model done
 - Now moving to analysis per module
- Annealing studies to be done
 - ▣ Heavy Ion period will be a good period (stable conditions and little radiation)
- Variation on V_{dep} not seen
 - ▣ New data has to be taken before the end of year



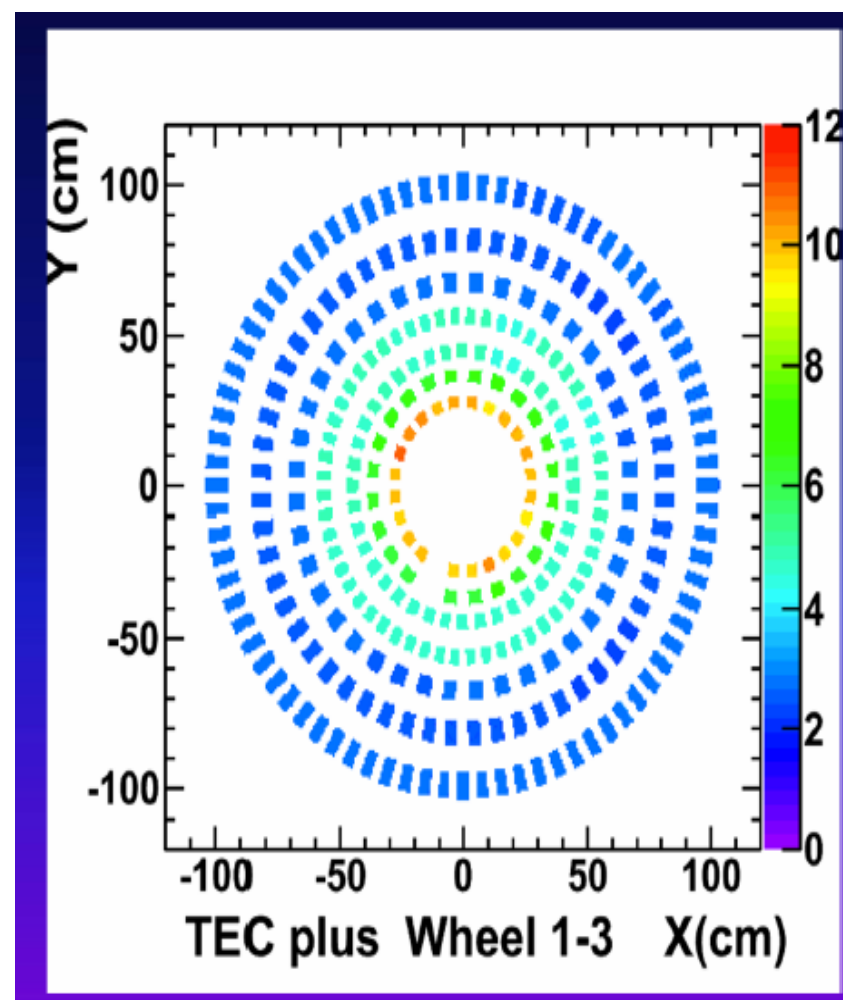
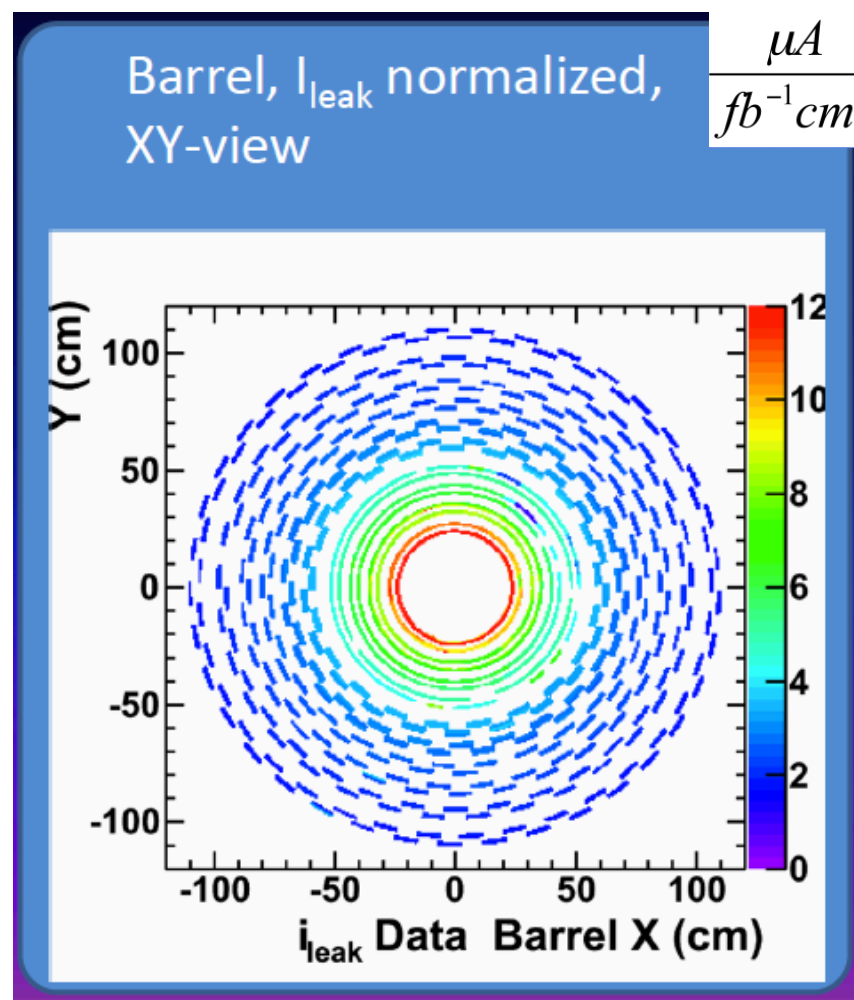
BCKUP SLIDES

Several Different Module Geometries

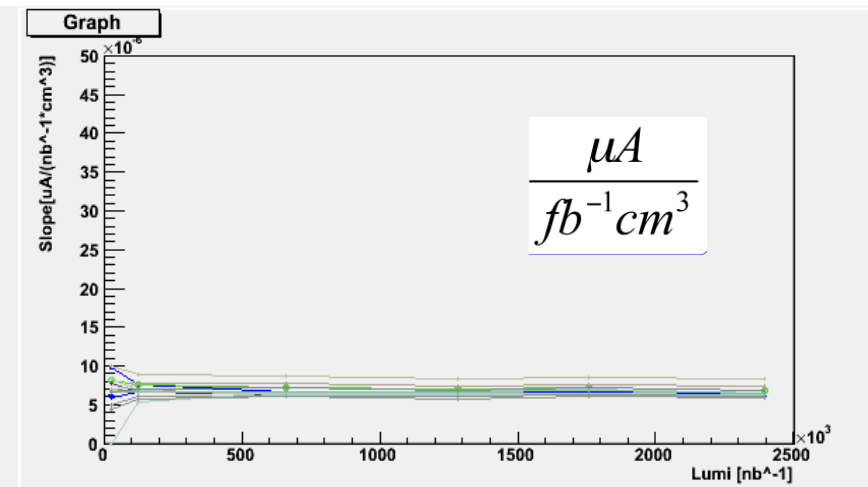
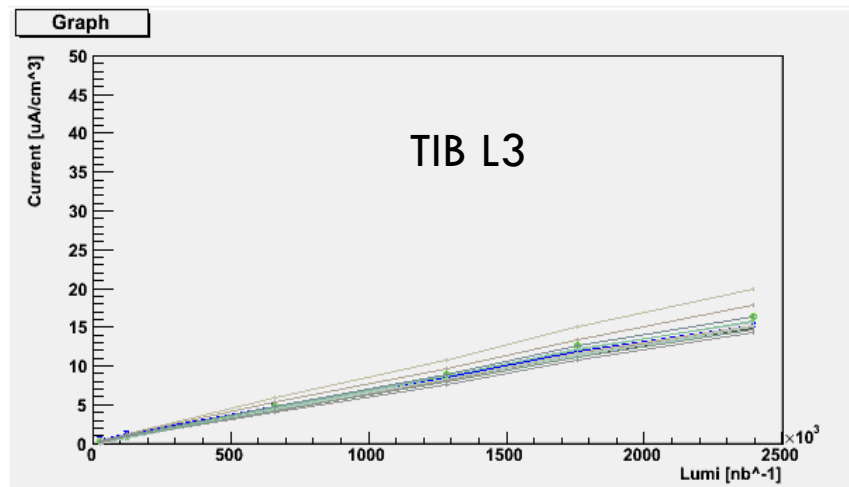
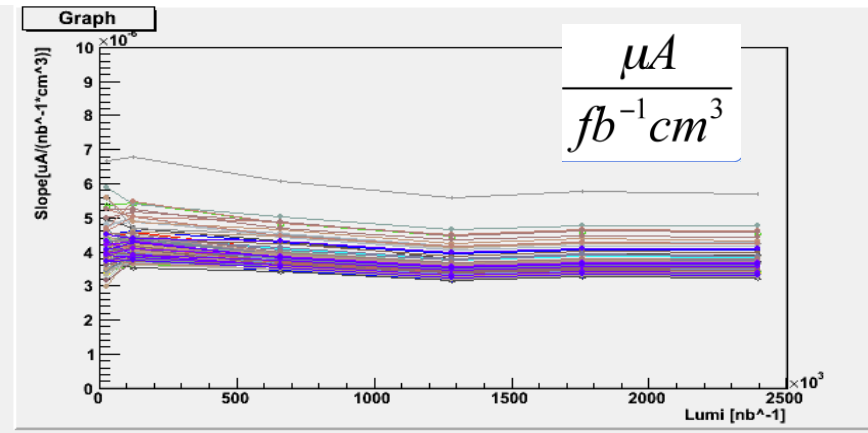
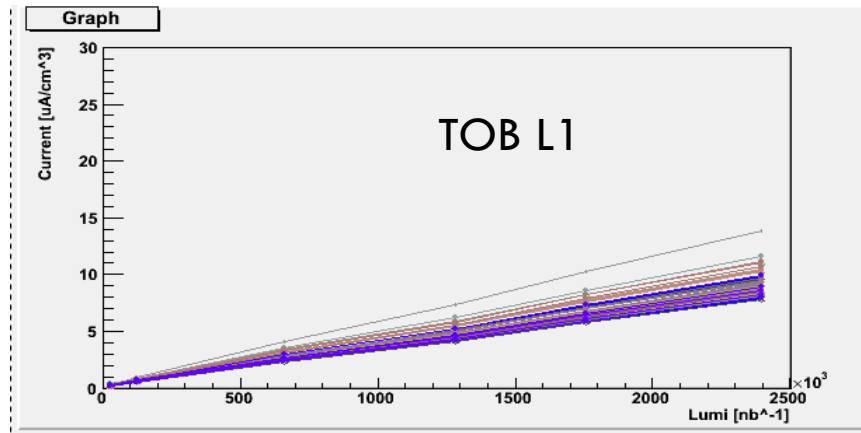
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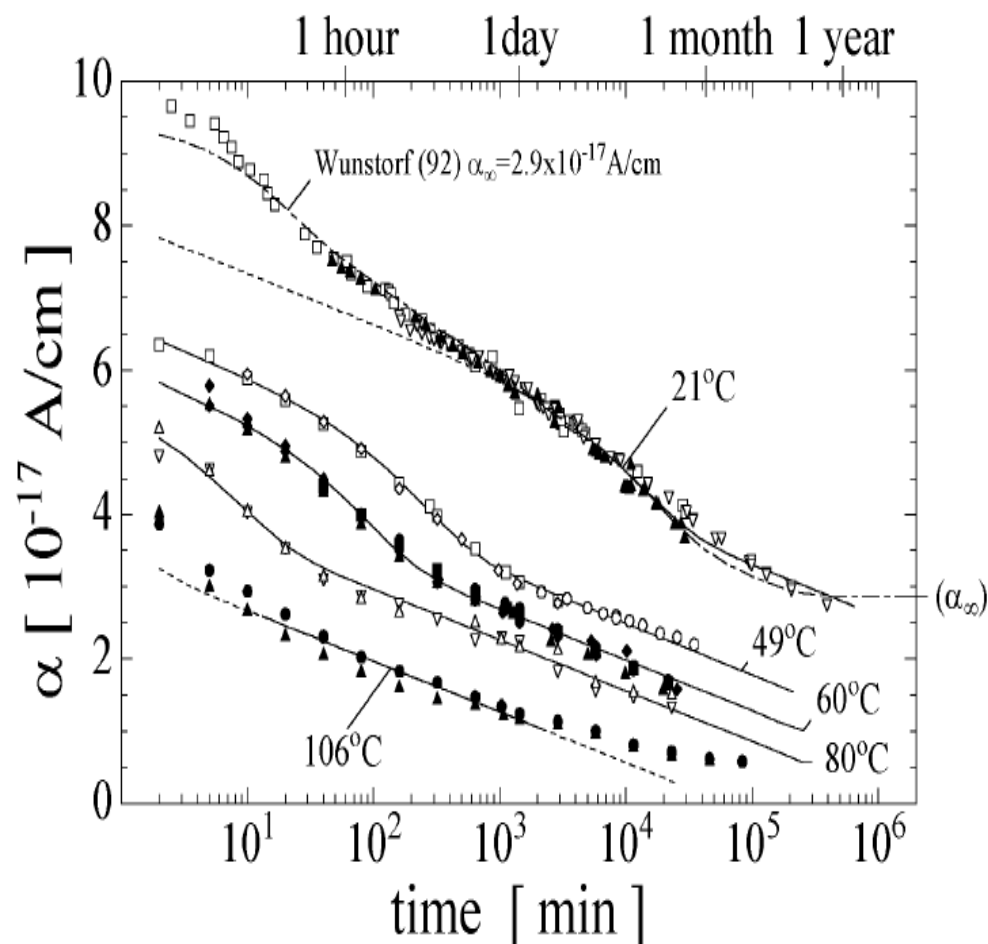
Geometry dependency of slope



Time dependence



Annealing modeling



- CMS SST uses extensively the annealing model for a wide range of temperatures
- Damage at LHC is provided as sum of many little “pills” with a time evolution: they are summed as independent one / another

Formulas for Leakage Current

- Temperature Scaling

$$I(T_1)/I(T_2) = (T_1/T_2)^2 \exp(-1.21/2k_B (1/T_1 - 1/T_2))$$

- Leakage Current Damage

$$\Delta I = \alpha \Phi V$$

- Annealing taken into account:

$$\begin{aligned} \alpha = & 1.23e-17 \text{ A/cm} \exp(-t/\tau_1) \\ & + -8.9e-17 \text{ A/cm} + 4.6 \text{ AK/cm} e^{-14/T} \\ & + 3.07e-18 \text{ A/cm} \ln(t/t_0) \end{aligned}$$

$$\text{and } 1/\tau_1 = 1.2e13 \exp(-1.12/2k_B T)$$

Formula for Depletion voltage

□ Full depletion voltage:

$$\Delta N_{\text{eff}} = N_A + N_C + N_Y$$

$$\text{with: } N_A = g_a \Phi \exp(-t/\tau_a)$$

$$N_C = 0.9 |N_{\text{eff}0}|^*$$

$$(1 - \exp(-10.9e-2/|N_{\text{eff}}| \Phi) + 1.77e-2 \Phi$$

$$N_Y = -g_Y \Phi (1 - 1/(1+t/\tau_Y))$$

$$\text{and } g_a = 1.54e-2 \text{ 1/cm}, g_Y = 4.6e-2 \text{ 1/cm}$$

$$\tau_a = 1/(2.3e13 \exp(-1.08/k_B T))$$

$$\tau_Y = 1/(1.5e15 \exp(-1.33/k_B T))$$